

SEMiX302GB176HDs



SEMiX® 2s

Trench IGBT Modules

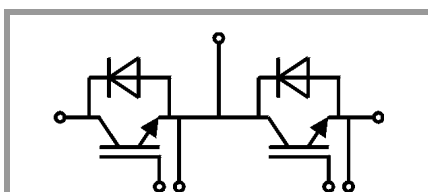
SEMiX302GB176HDs

Features

- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders



GB

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		1700	V
I _C	T _j = 150 °C	T _c = 25 °C	308	A
		T _c = 80 °C	219	A
I _{Cnom}			200	A
I _{CRM}	I _{CRM} = 2xI _{Cnom}		400	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 1000 V V _{GE} ≤ 20 V V _{CES} ≤ 1700 V	T _j = 125 °C	10	μs
T _j			-55 ... 150	°C
Inverse diode				
I _F	T _j = 150 °C	T _c = 25 °C	389	A
		T _c = 80 °C	262	A
I _{Fnom}			200	A
I _{FRM}	I _{FRM} = 2xI _{Fnom}		400	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		2000	A
T _j			-40 ... 150	°C
Module				
I _{t(RMS)}	T _{terminal} = 80 °C		600	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 200 A	T _j = 25 °C		2	2.45	V
	V _{GE} = 15 V chiplevel	T _j = 125 °C		2.5	2.9	V
V _{CE0}		T _j = 25 °C		1	1.2	V
		T _j = 125 °C		0.9	1.1	V
r _{CE}	V _{GE} = 15 V	T _j = 25 °C		5.0	6.3	mΩ
		T _j = 125 °C		7.8	9.0	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 8 mA		5.2	5.8	6.4	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C				mA
	V _{CE} = 1700 V	T _j = 125 °C				mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		17.6		nF
C _{oes}		f = 1 MHz		0.73		nF
C _{res}		f = 1 MHz		0.58		nF
Q _G	V _{GE} = - 8 V...+ 15 V			1866		nC
R _{Gint}	T _j = 25 °C			3.75		Ω
t _{d(on)}	V _{CC} = 1200 V	T _j = 125 °C		225		ns
t _r	I _C = 200 A	T _j = 125 °C		45		ns
E _{on}	V _{GE} = ±15 V	T _j = 125 °C		130		mJ
t _{d(off)}	R _{G on} = 6.5 Ω	T _j = 125 °C		665		ns
t _f	R _{G off} = 6.5 Ω	T _j = 125 °C		105		ns
E _{off}		T _j = 125 °C		77		mJ
R _{th(j-c)}	per IGBT				0.1	K/W

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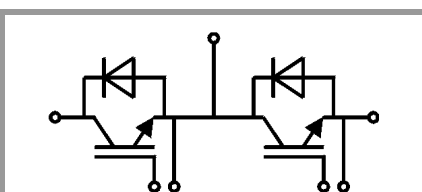
Features

- Homogeneous Si
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Typical Applications*

- AC inverter drives
- UPS
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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
V _F = V _{EC}	I _F = 200 A V _{GE} = 0 V chip	T _j = 25 °C		1.5	1.70	V
		T _j = 125 °C		1.4	1.6	V
V _{F0}		T _j = 25 °C	0.9	1.1	1.3	V
		T _j = 125 °C	0.7	0.9	1.1	V
r _F		T _j = 25 °C	2.0	2.0	2.0	mΩ
		T _j = 125 °C	2.7	2.7	2.7	mΩ
I _{RRM}	I _F = 200 A	T _j = 125 °C	235			A
Q _{rr}	di/dt _{off} = 3100 A/μs	T _j = 125 °C	77			μC
E _{rr}	V _{GE} = -15 V V _{CC} = 1200 V	T _j = 125 °C	43			mJ
R _{th(j-c)}	per diode		0.15			K/W
Module						
L _{CE}			18			nH
R _{CC'+EE'}	res., terminal-chip	T _C = 25 °C	0.7			mΩ
		T _C = 125 °C	1			mΩ
R _{th(c-s)}	per module		0.045			K/W
M _s	to heat sink (M5)		3	5		Nm
M _t		to terminals (M6)	2.5	5		Nm
				Nm		
w			250			g
Temperatur Sensor						
R ₁₀₀	T _c =100°C (R ₂₅ =5 kΩ)		493 ± 5%			Ω
B _{100/125}	R _(T) =R ₁₀₀ exp[B _{100/125} (1/T-1/T ₁₀₀)]; T[K];		3550 ±2%			K



GB

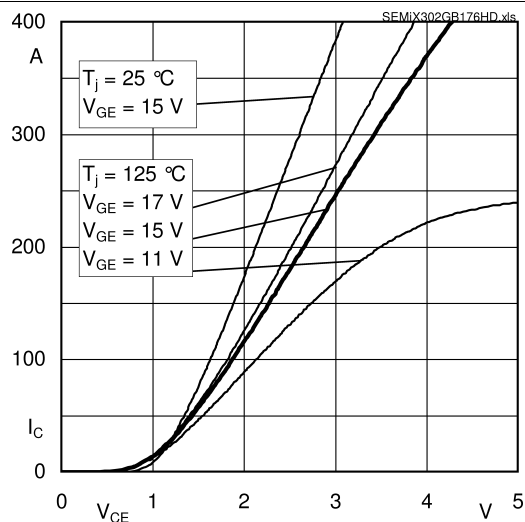


Fig. 1: Typ. output characteristic, inclusive $R_{CC} + EE'$

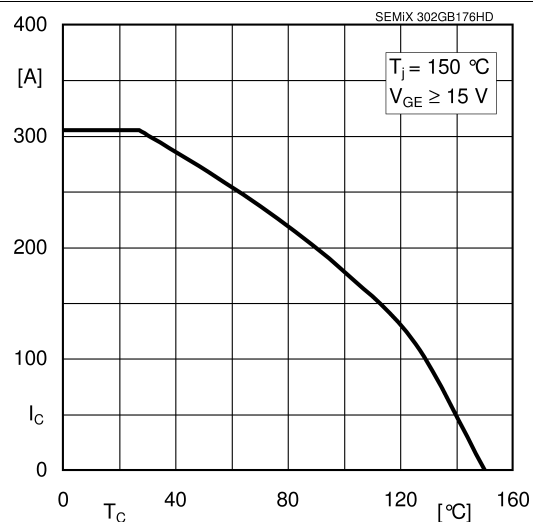


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

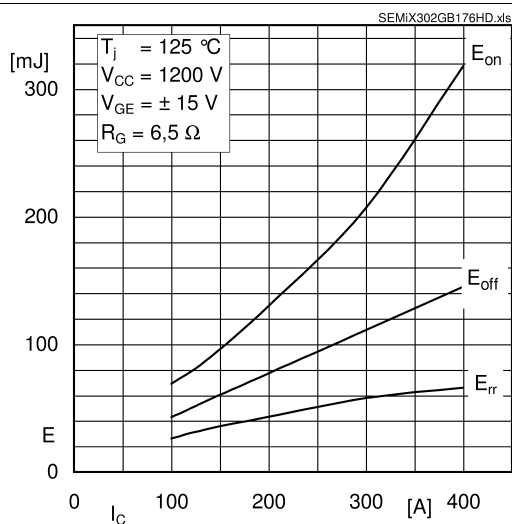


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

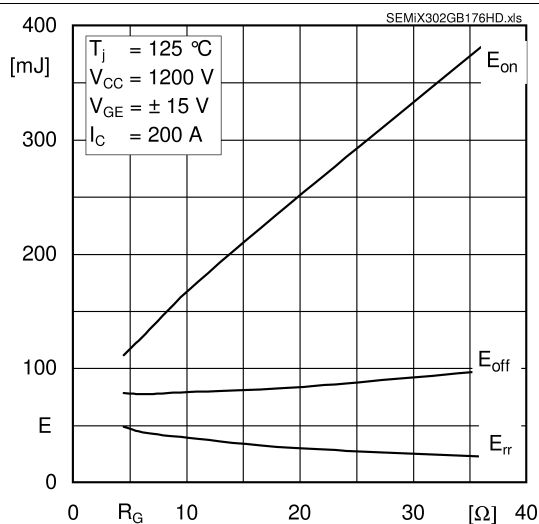


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

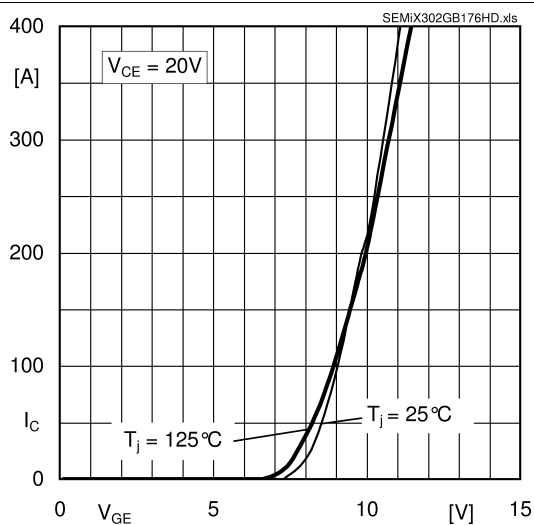


Fig. 5: Typ. transfer characteristic

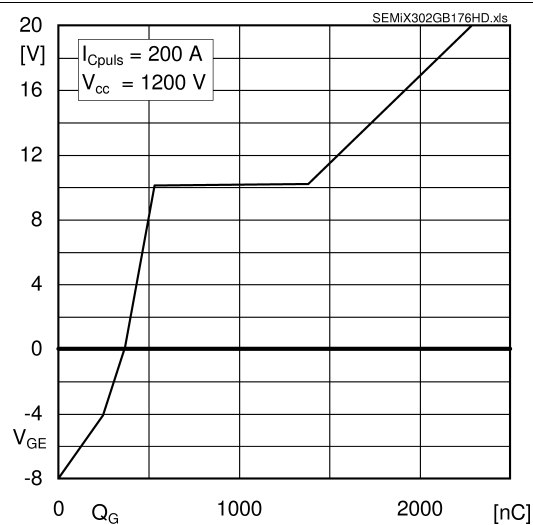


Fig. 6: Typ. gate charge characteristic

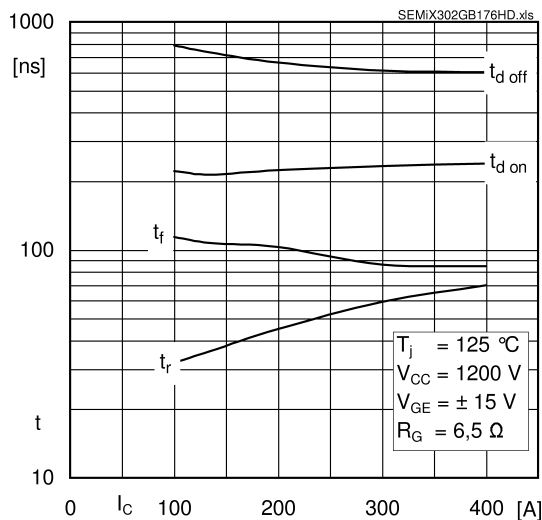


Fig. 7: Typ. switching times vs. I_C

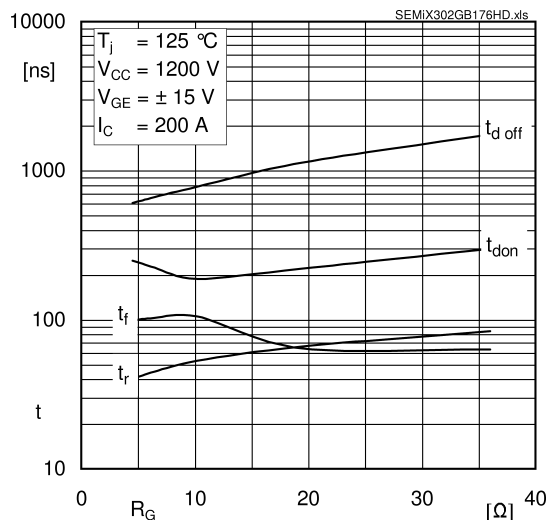


Fig. 8: Typ. switching times vs. gate resistor R_G

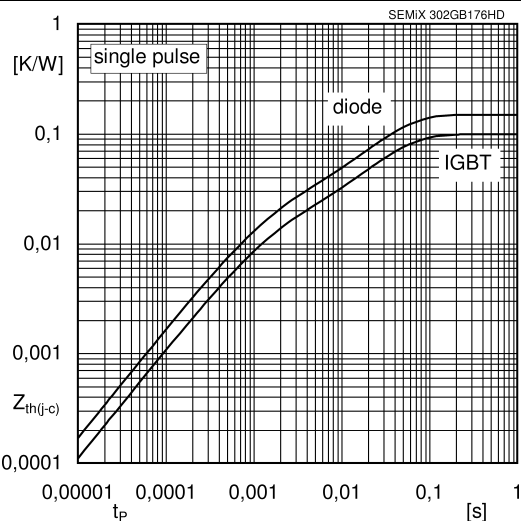


Fig. 9: Typ. transient thermal impedance

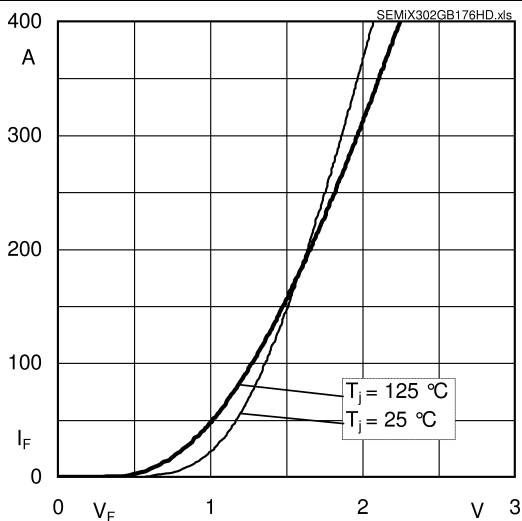


Fig. 10: Typ. CAL diode forward charact., incl. $R_{CC'+EE'}$

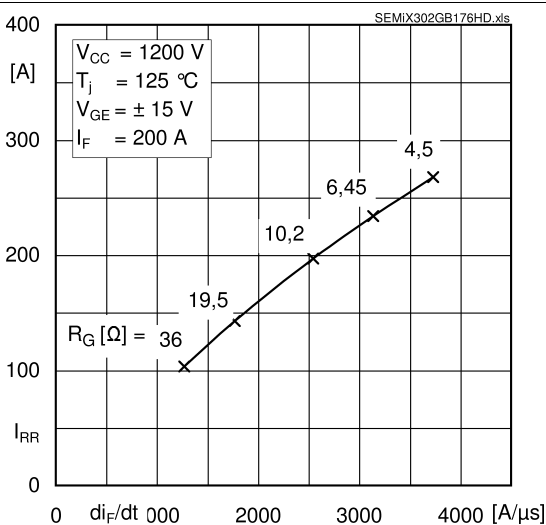


Fig. 11: Typ. CAL diode peak reverse recovery current

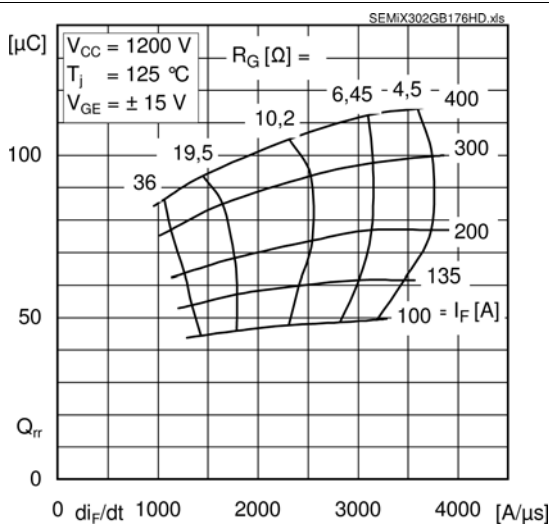


Fig. 12: Typ. CAL diode recovery charge

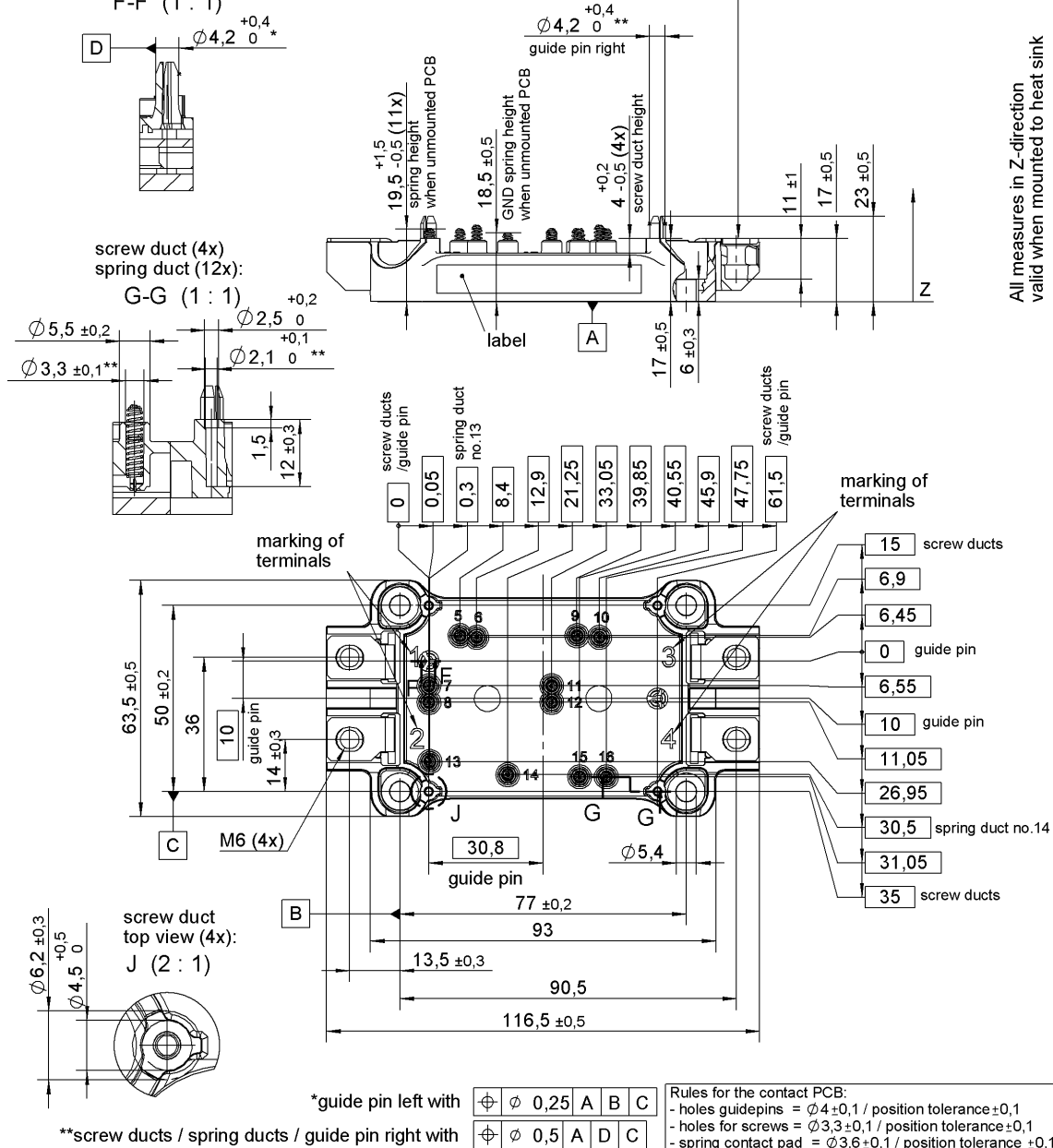
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guide pin left
F-F (1 : 1)

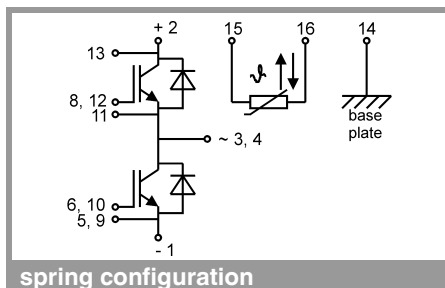
	0,3	connector 1-2 / 3-4
	0,2	each connector

general tolerance:
ISO 2768-m
ISO 8015



All measures in Z-direction
valid when mounted to heat sink

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This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.